060401  Coupling between quantum dots and photonic nanostructures
         Xin Xie, Shushu Shi, and Xiulai Xu

061101  A brief review of formation energies calculation of surfaces and edges in
         semiconductors
         Chuen-Keung Sin, Jingzhao Zhang, Kinfai Tse, and Junyi Zhu

061401  A review on performance comparison of advanced MOSFET structures
         below 45 nm technology node
         Namrata Mendiratta and Suman Lata Tripathi

062301  Modelling and optical response of a compressive-strained AlGaN/GaN quantum
         well laser diode
         A. Menani, L. Dehimi, S. Dehimi, and F. Pezzimenti

062302  Strain-induced the dark current characteristics in InAs/GaSb type-II superlattice
         for mid-wave detector

062303  1064 nm InGaAsP multi-junction laser power converters
         Jiajing Yin, Yurun Sun, Shuzhen Yu, Yongming Zhao, Rongwei Li, and Jianrong Dong

062401  A 0.1–1.5 GHz multi-octave quadruple-stacked CMOS power amplifier
         Shizhe Wei, Haifeng Wu, Qian Lin, and Mingzhe Zhang

062402  A high performance adaptive on-time controlled valley-current-mode DC–DC
         buck converter
         Chanrong Jiang, Changchun Chai, Chenxi Han, and Yintang Yang

062403  Variation tolerance for high-speed negative capacitance FinFET SRAM bit cell
         Yaqian Qian, Shushan Qiao, and Rongqiang Yang

062404  An 18-bit sigma–delta switched-capacitor modulator using 4-order single-loop
         CIFB architecture
         Guiping Cao and Ning Dong

062601  Mathematical analysis of organic-pass transistor using pseudo-p-OTFTs
         Shagun Pal and Brijesh Kumar
<table>
<thead>
<tr>
<th>Page</th>
<th>Title</th>
<th>Authors</th>
</tr>
</thead>
<tbody>
<tr>
<td>062701</td>
<td><strong>Numerical study of mono-crystalline silicon solar cells with passivated emitter and rear contact configuration for the efficiency beyond 24% based on mass production technology</strong></td>
<td>Peng Wang, Gaofei Li, Miao Wang, Hong Li, Jing Zheng, Liyou Yang, Yigang Chen, Dongdong Li, and Linfeng Lu</td>
</tr>
<tr>
<td>062801</td>
<td><strong>Low on-resistance 1.2 kV 4H-SiC power MOSFET with $R_{on,sp}$ of 3.4 mΩ·cm$^2$</strong></td>
<td>Qiang Liu, Qian Wang, Hao Liu, Chenxi Fei, Shiyan Li, Runhua Huang, and Song Bai</td>
</tr>
</tbody>
</table>